

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-12. (Canceled)

13. (Previously Presented) A silicon single crystal wafer grown by the Czochralski method, which is doped with nitrogen, and has an N-region for the entire plane and an interstitial oxygen concentration of 5-8 ppma.

14. (Previously Presented) A silicon single crystal wafer grown by the Czochralski method, which is doped with nitrogen, and has an interstitial oxygen concentration of 5-8 ppma, and in which at least void type defects and dislocation clusters are eliminated from the entire plane.

15. (Previously Presented) A silicon single crystal wafer, which is doped with nitrogen, has an N-region for the entire plane, and has an interstitial oxygen concentration of 5 ppma or less, and one main surface of the silicon single crystal wafer is subjected to an EG treatment.

16. (Previously Presented) A silicon single crystal wafer, which is doped with nitrogen, has an interstitial oxygen concentration of 5 ppma or less, in which at least void type defects and dislocation clusters are eliminated from the entire plane, and the main surface of the silicon single crystal wafer is subjected to an EG treatment.

17. (Previously Presented) The silicon single crystal wafer according to Claim 13, wherein the concentration of the doped nitrogen is 1×10^{14} number/cm³ or more.

18. (Previously Presented) The silicon single crystal wafer according to Claim 14, wherein the concentration of the doped nitrogen is 1×10^{14} number/cm³ or more.

19. (Previously Presented) The silicon single crystal wafer according to Claim 13, wherein the concentration of the doped nitrogen is 5×10^{14} number/cm³ or more.

20. (Previously Presented) The silicon single crystal wafer according to Claim 14, wherein the concentration of the doped nitrogen is 5×10^{14} number/cm³ or more.

21. (Previously Presented) The silicon single crystal wafer according to Claim 13, wherein one main surface of the silicon single crystal wafer is subjected to an EG treatment.

22. (Previously Presented) The silicon single crystal wafer according to Claim 14, wherein one main surface of the silicon single crystal wafer is subjected to an EG treatment.

23. (Previously Presented) An SOI wafer, wherein a silicon single crystal wafer according to Claim 13 is used as an SOI layer.

24. (Previously Presented) An SOI wafer, wherein a silicon single crystal wafer according to Claim 14 is used as an SOI layer.

25. (Previously Presented) A method for producing a silicon single crystal wafer, wherein the wafer is produced from a single crystal pulled under such conditions that the crystal should have an N-region for the entire plane and interstitial oxygen concentration should become 5-8 ppma when the crystal is grown by the Czochralski method with nitrogen doping.

26. (Previously Presented) The method for producing a silicon single crystal wafer according to Claim 25, wherein the wafer is produced from a single crystal grown with a concentration of doped nitrogen of 1×10^{14} number/cm³ or more and an F/G value (F: pulling rate, G: crystal solid-liquid interface temperature gradient) in a range of 0.14-0.22 mm²/K•min at any point of crystal plane as such a condition that the entire plane of the crystal should become an N-region.

27. (Previously Presented) The method for producing a silicon single crystal wafer according to Claim 25, wherein the wafer is produced from a single crystal grown with a concentration of doped nitrogen of 5×10^{14} number/cm³ or more and an F/G value in a range

of $0.12\text{-}0.24\text{ mm}^2/\text{K}\cdot\text{min}$ at any point of crystal plane as such a condition that the entire plane of the crystal should become an N-region.

28. (Previously Presented) A method for producing a silicon single crystal wafer, wherein a silicon single crystal wafer produced by a production method according to Claim 25 is subjected to a heat treatment.

29. (Previously Presented) A method for producing a silicon single crystal wafer, wherein a silicon single crystal wafer produced by a production method according to Claim 26 is subjected to a heat treatment.

30. (Currently Amended) A method for producing a silicon single crystal wafer, wherein a silicon single crystal wafer produced by a production method according to ~~Claims~~ Claim 27 is subjected to a heat treatment.

31. (Previously Presented) The method for producing a silicon single crystal wafer according to Claim 28, wherein the heat treatment is performed by using a rapid thermal annealer.

32. (Previously Presented) The method for producing a silicon single crystal wafer according to Claim 29, wherein the heat treatment is performed by using a rapid thermal annealer.

33. (Previously Presented) The method for producing a silicon single crystal wafer according to Claim 30, wherein the heat treatment is performed by using a rapid thermal annealer.